

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Byung-Sup SHIM et al.

Serial No. 09/305,240

Examiner: O. Nadav

Filed: May 4, 1999

Group Art Unit: 2811

For: OPEN DRAIN INPUT/OUTPUT STRUCTURE AND
MANUFACTURING METHOD THEREOF IN SEMICONDUCTOR
DEVICE

Box CPA
Assistant Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows

IN THE SPECIFICATION

On page 2, line 25, replace "FIG.s" with --FIGs.--;

On page 4, line 9, replace "a n-type" with --an n-type--.

IN THE CLAIMS:

Please amend claim 9 as follows:

9. (Twice Amended) The transistor of claim 5, wherein the first sector
is separated from the source region and from the drain region by substantially equal
distances.

REMARKS

In this case, a Final Office Action was mailed on 8-31-2000. All pending
claims [namely 5-7, 9] were rejected.

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Harrison

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